

High Voltage Standard Rectifier Module

$$V_{RRM} = 2 \times 2200 \text{ V}$$

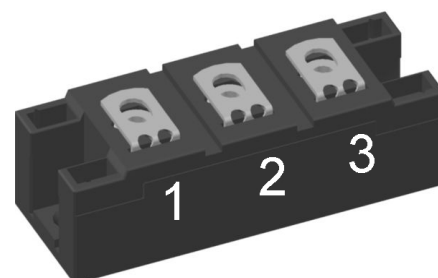
$$I_{FAV} = 224 \text{ A}$$

$$V_F = 1.07 \text{ V}$$

Phase leg

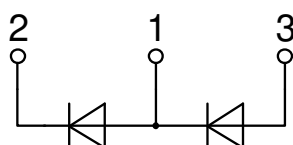
Part number

MDD200-22N1



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: Y4

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				2300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				2200	V
I_R	reverse current	$V_R = 2200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1	mA
		$V_R = 2200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			20	mA
V_F	forward voltage drop	$I_F = 300\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.16	V
		$I_F = 600\text{ A}$				1.39	V
		$I_F = 300\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.07	V
		$I_F = 600\text{ A}$				1.36	V
I_{FAV}	average forward current	$T_C = 100^{\circ}\text{C}$	$T_{VJ} = 150^{\circ}\text{C}$			224	A
$I_{F(RMS)}$	RMS forward current	180° sine $d = 0.5$				350	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.80	V
r_F	slope resistance					0.6	mΩ
R_{thJC}	thermal resistance junction to case					0.13	K/W
R_{thCH}	thermal resistance case to heatsink				0.08		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				960	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			10.5	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			11.3	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			8.93	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			9.64	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			551.3	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			535.0	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			398.3	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			386.6	kA ² s
C_J	junction capacitance	$V_R = 1100\text{ V}; f = 1\text{ MHz}$		$T_{VJ} = 25^{\circ}\text{C}$	230		pF

Package Y4				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				300	A
T _{VJ}	virtual junction temperature			-40		150	°C
T _{op}	operation temperature			-40		125	°C
T _{stg}	storage temperature			-40		125	°C
Weight					150		g
M _D	mounting torque			2.25		2.75	Nm
M _T	terminal torque			4.5		5.5	Nm
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	14.0	10.0			mm
d _{Spb/Apb}		terminal to backside	16.0	16.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	3600			V
		t = 1 minute		3000			V



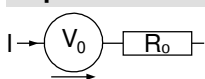
Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

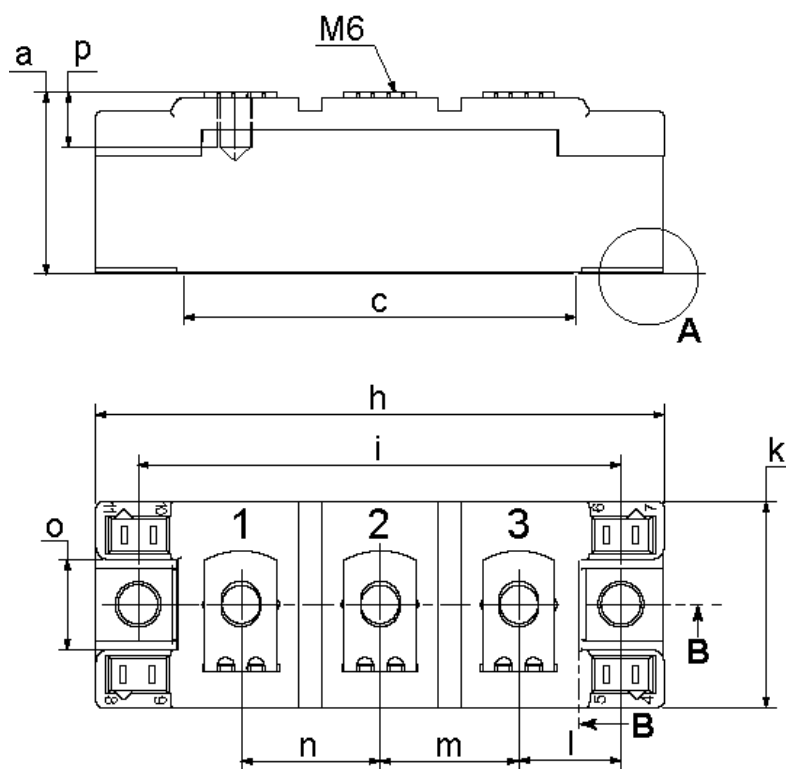
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD200-22N1	MDD200-22N1	Box	6	500701

Equivalent Circuits for Simulation

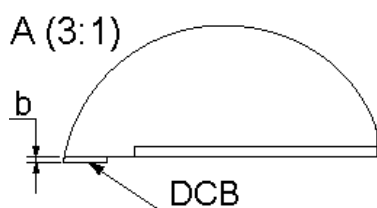
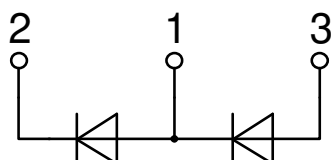
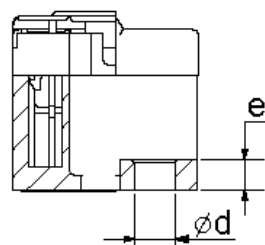
* on die level

$T_{VJ} = 150^{\circ}\text{C}$

			
$V_{0\max}$	threshold voltage	0.8	V
$R_{0\max}$	slope resistance *	0.4	mΩ

Outlines Y4


Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
a	30.0	30.6	1.181	1.205
b	typ. 0.25		typ. 0.010	
c	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
e	4.9	5.1	0.193	0.201
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
k	33.4	34.0	1.315	1.339
l	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
o	14.0	15.0	0.551	0.591
p	typ. 10.5		typ. 0.413	


B-B (1:1)


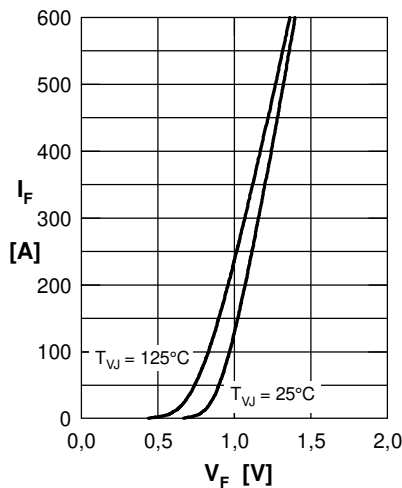
Rectifier


Fig. 1 Forward current versus voltage drop

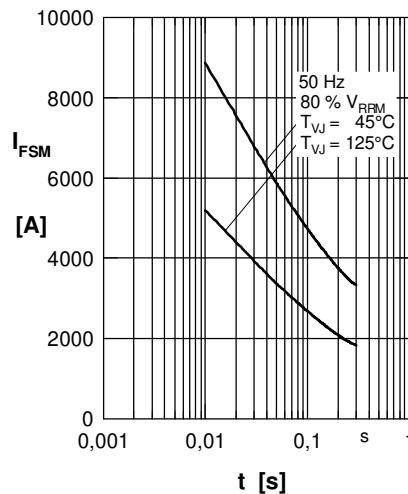


Fig. 2 Surge overload current
 I_{FSM} : Crest value, t : duration

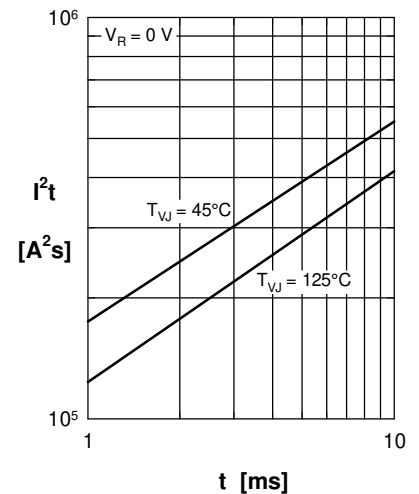


Fig. 3 I^2t versus time (1-10 ms)

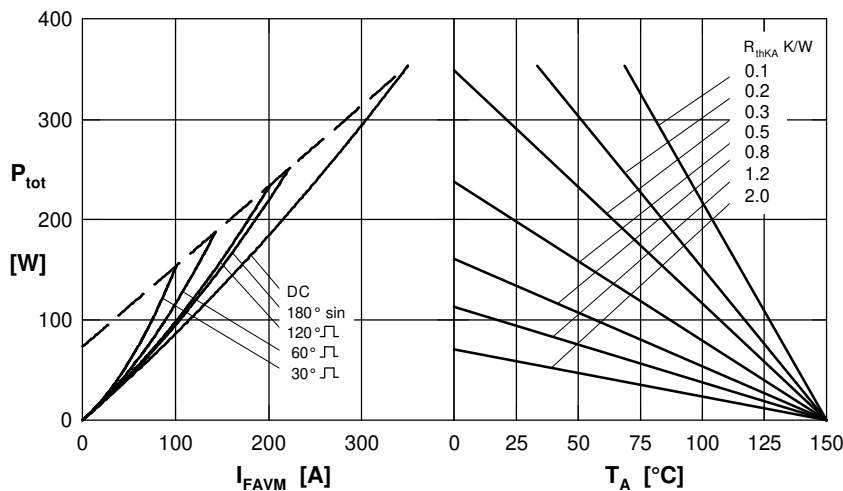


Fig. 4 Power dissipation versus forward current and ambient temperature (per diode)

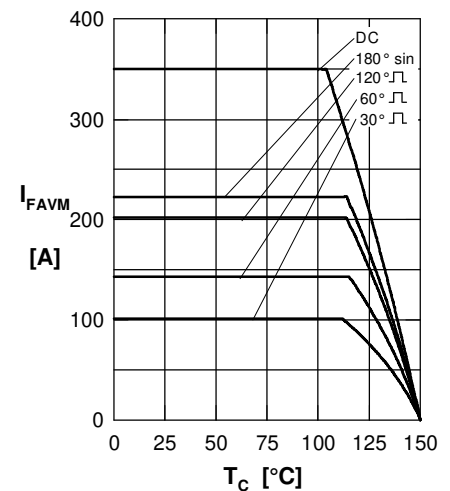


Fig. 5 Maximum forward current at case temperature

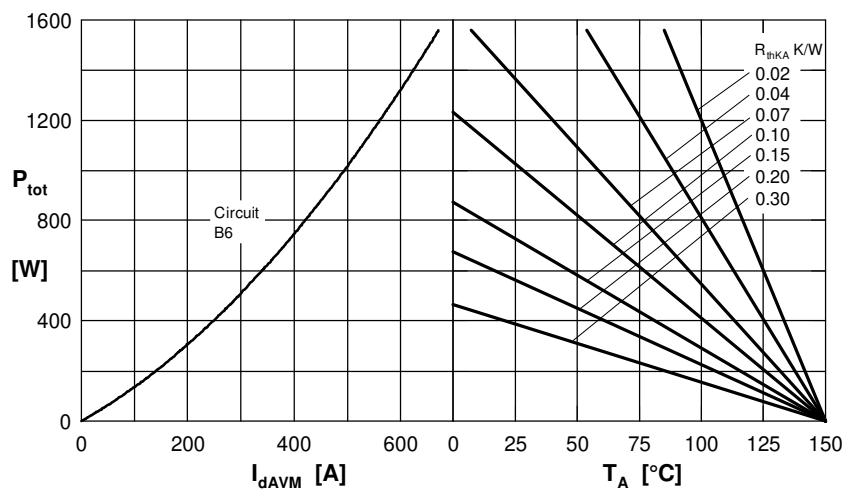


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

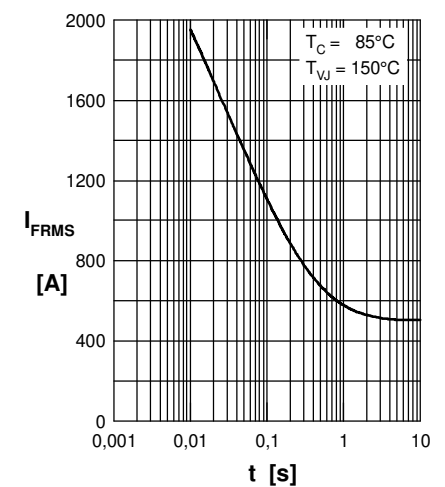
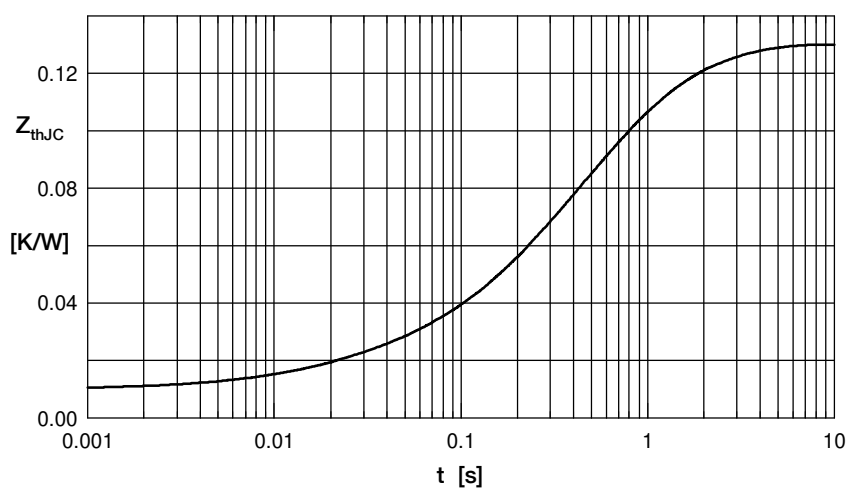


Fig. 7 Rated RMS current versus time (360° conduction)

Rectifier

 Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.0100	0.00014
2	0.0065	0.019
3	0.0250	0.180
4	0.0615	0.520
5	0.0270	1.600

Fig. 8 Transient thermal impedance junction to case